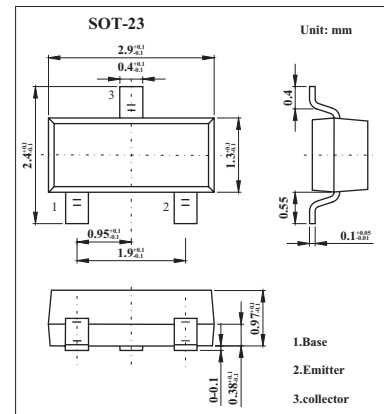


PNP Epitaxial Planar Silicon Transistor

2SA1580

■ Features

- High fr.
- Small reverse transfer capacitance.
- Adoption of FBET process.



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CB0}	-70	V
Collector-emitter voltage	V _{CEO}	-60	V
Emitter-base voltage	V _{EBO}	-4	V
Collector current	I _C	-50	mA
Collector current (pulse)	I _{CP}	-100	mA
Collector dissipation	P _C	200	mW
Junction temperature	T _J	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector cutoff current	I _{CBO}	V _{CB} = -40V, I _E = 0			-0.1	μA
Emitter cutoff current	I _{EBO}	V _{EB} = -3V, I _C = 0			-1	μA
DC current gain	h _{FE}	V _{CE} = -10V, I _C = -10mA	60		270	
Gain bandwidth product	f _T	V _{CE} = -10V, I _C = -10mA	350	700		MHz
Base-collector time constant	r _{bb,cc}	V _{CE} = -10V, I _C = -10mA		8		ps
Output capacitance	C _{ob}	V _{CB} = -10V, f = 1.0MHz		1.7		pF
Reverse transfer capacitance	C _{re}	V _{CB} = -10V, f = 1.0MHz		1.3		pF
Collector-emitter saturation voltage	V _{CE(sat)}	I _C = -20mA, I _B = -2mA			-0.6	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C = -20mA, I _B = -2mA			-1	V
Collector-base breakdown voltage	V _{(BR)CBO}	I _C = -10μA, I _E = 0	-70			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C = -1mA, R _{BE} = ∞	-60			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E = -10μA, I _C = 0	-4			V

■ hFE Classification

Marking	QL		
	3	4	5
hFE	60~120	90~180	135~270